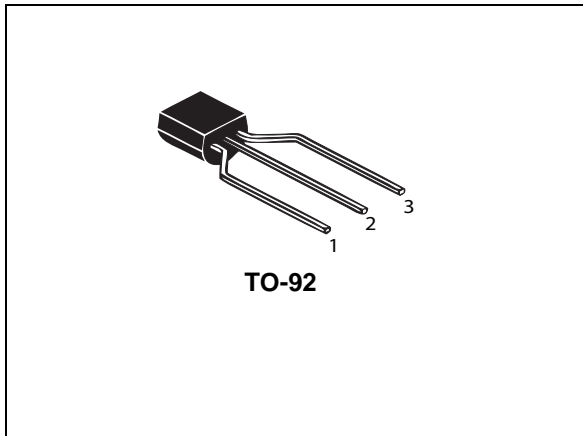


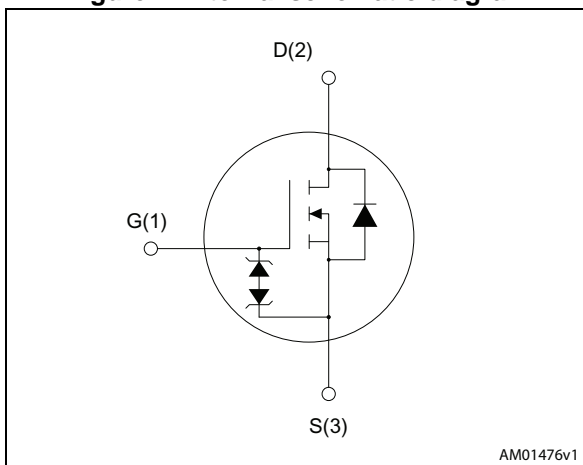
## N-channel 450 V - 3.3 $\Omega$ typ., 0.6 A Zener-protected, SuperMESH3™ Power MOSFET in a TO-92 package

Datasheet - production data



TO-92

Figure 1. Internal schematic diagram



### Features

Order code	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>	P <sub>w</sub>
STQ3N45K3-AP	450 V	< 4 $\Omega$	0.6 A	3 W

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

### Applications

- Switching applications

### Description

This SuperMESH3™ Power MOSFET is the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. This device boasts an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering it suitable for the most demanding applications.

Table 1. Device summary

Order code	Marking	Package	Packaging
STQ3N45K3-AP	3N45K3	TO-92	Ammopak

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	450	V
$V_{GS}$	Gate- source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	0.6	A
$I_{DM}^{(1)}$	Drain current (pulsed)	2.4	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	3	W
$I_{AR}^{(2)}$	Avalanche current, repetitive or not-repetitive	0.6	A
$E_{AS}^{(3)}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{V}$ )	45	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	12	V/ns
Vesd(g-s)	G-S ESD (HBM C = 100 pF, R = 1.5 k $\Omega$ )	1000	V
$T_{stg}$	Storage temperature	-55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. Pulse width limited by  $T_{j\text{ max}}$ .
3. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$ .
4.  $I_{SD} \leq 0.6\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-ambient	42	$^\circ\text{C}/\text{W}$

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	450			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 450\text{ V}$ $V_{DS} = 450\text{ V}$ , $T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 0.6\text{ A}$		3.3	4	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	164	-	pF
$C_{oss}$	Output capacitance		-	17	-	pF
$C_{riss}$	Reverse transfer capacitance		-	3	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }360\text{ V}$ , $V_{GS} = 0$	-	13	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	18	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	8	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 360\text{ V}$ , $I_D = 1.8\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> )	-	9.5	-	nC
$Q_{gs}$	Gate-source charge		-	2	-	nC
$Q_{gd}$	Gate-drain charge		-	6	-	nC

- $C_{oss\text{ eq}}$  time related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$
- $C_{oss\text{ eq}}$  energy related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 225\text{ V}$ , $I_D = 0.9\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15</a> )	-	6.5	-	ns
$t_r$	Rise time		-	5.4	-	ns
$t_{d(off)}$	Turn-off-delay time		-	17	-	ns
$t_f$	Fall time		-	22	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		0.6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		2.4	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 0.6\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 1.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 20</a> )	-	175		ns
$Q_{rr}$	Reverse recovery charge		-	550		nC
$I_{RRM}$	Reverse recovery current		-	6		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 1.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 20</a> )	-	185		ns
$Q_{rr}$	Reverse recovery charge		-	600		nC
$I_{RRM}$	Reverse recovery current		-	6.5		A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device's ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

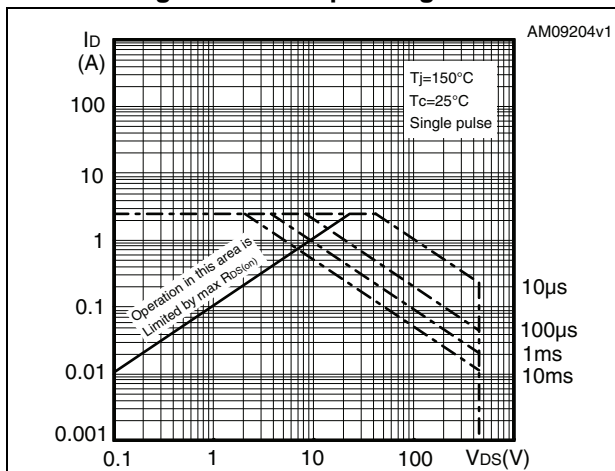


Figure 3. Thermal impedance

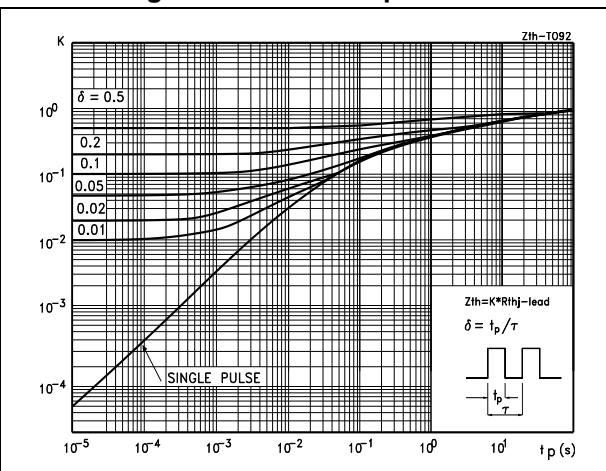


Figure 4. Output characteristics

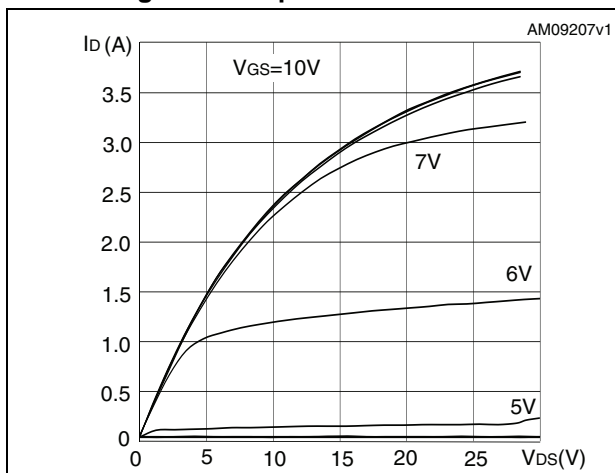


Figure 5. Transfer characteristics

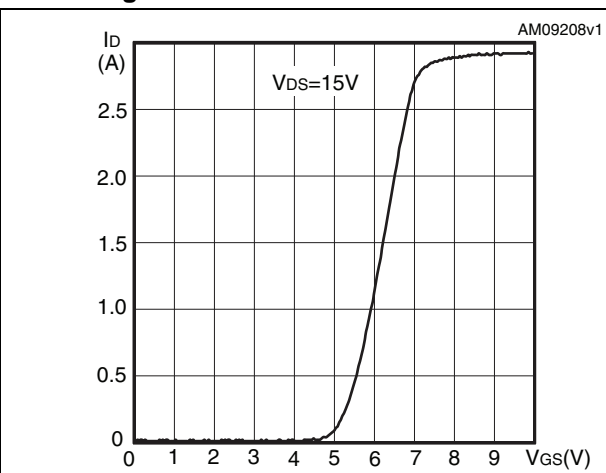


Figure 6. Gate charge vs gate-source voltage

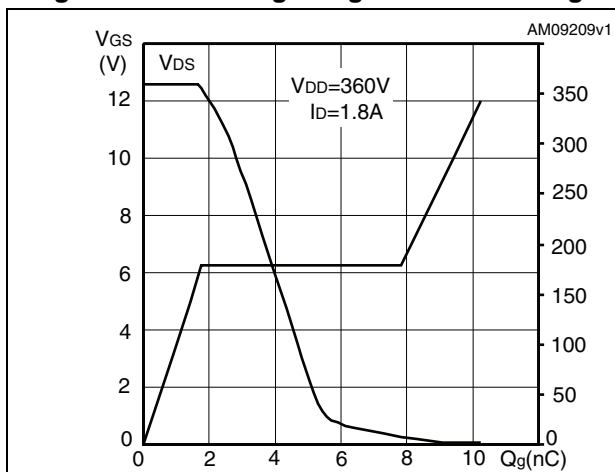


Figure 7. Static drain-source on resistance

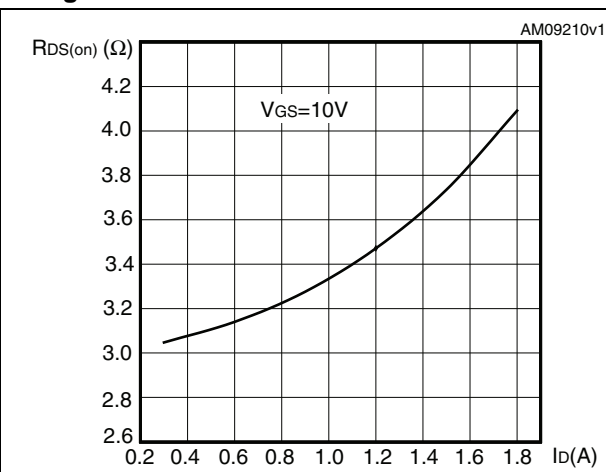


Figure 8. Capacitance variations

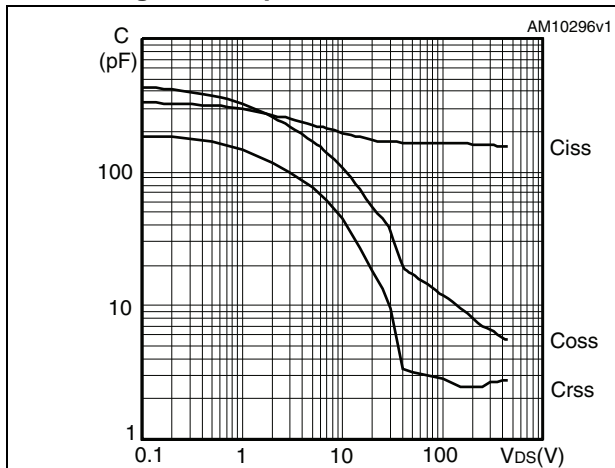


Figure 9. Output capacitance stored energy

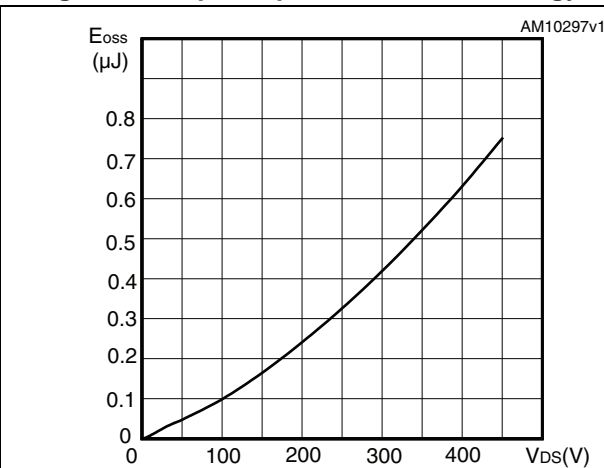


Figure 10. Normalized gate threshold voltage vs temperature

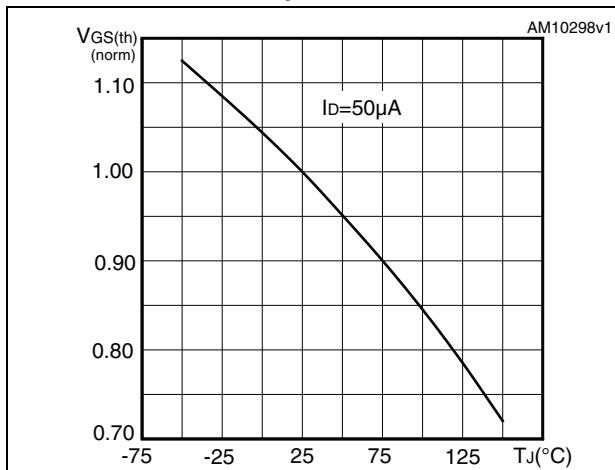


Figure 11. Normalized on-resistance vs temperature

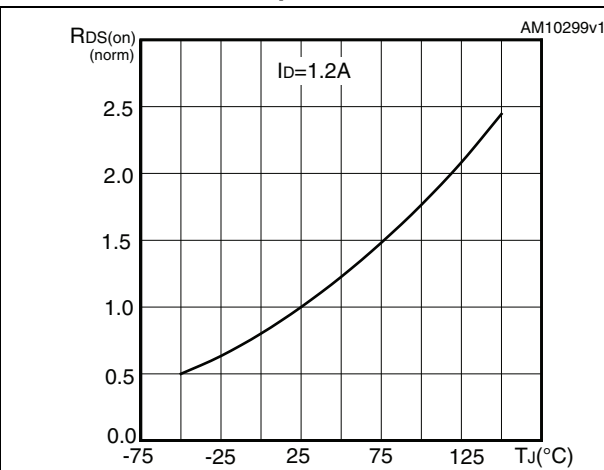


Figure 12. Source-drain diode forward characteristics

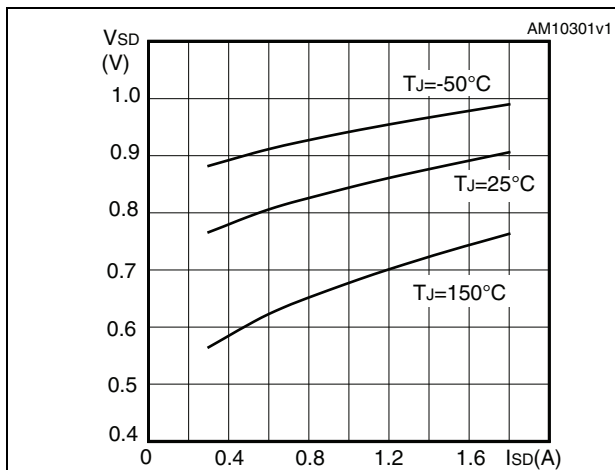


Figure 13. Normalized BV<sub>DSS</sub> vs temperature

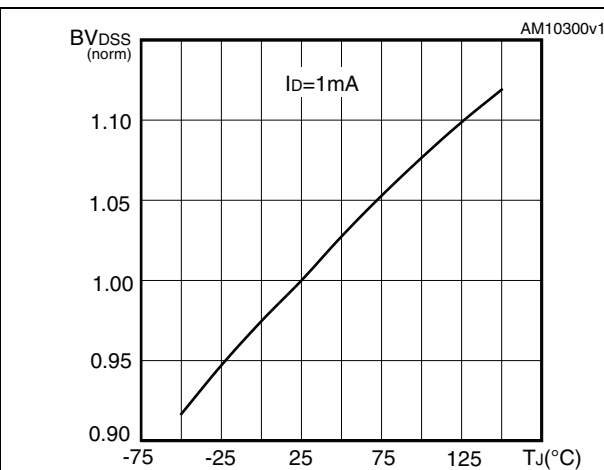
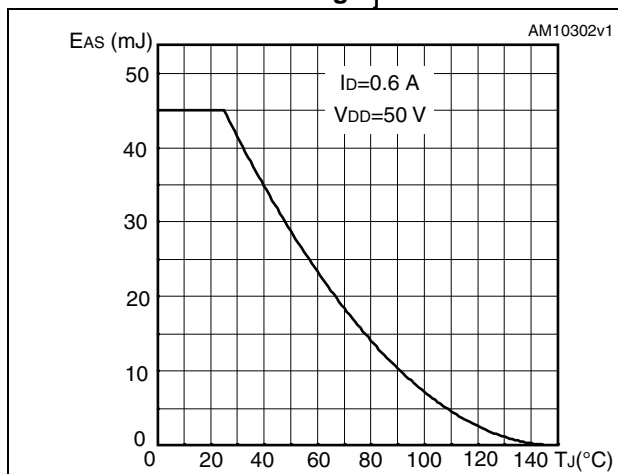


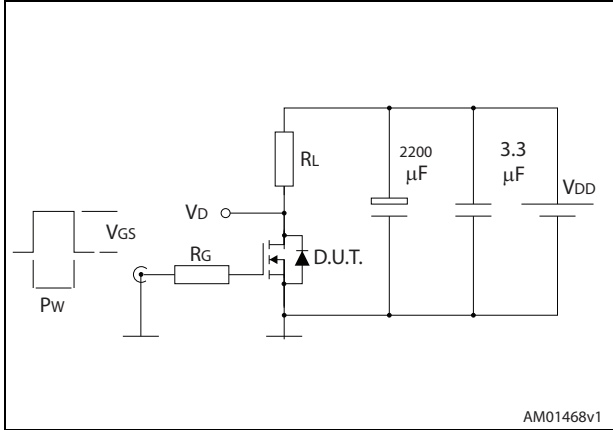
Figure 14. Maximum avalanche energy vs starting  $T_j$



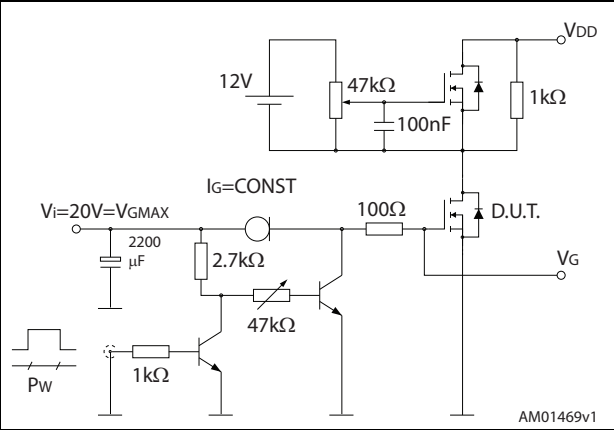


### 3 Test circuits

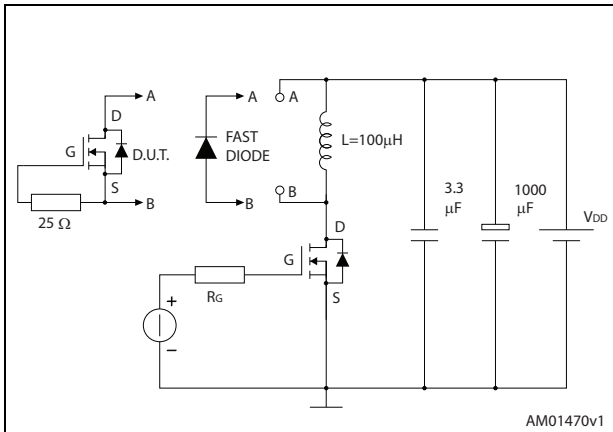
**Figure 15. Switching times test circuit for resistive load**



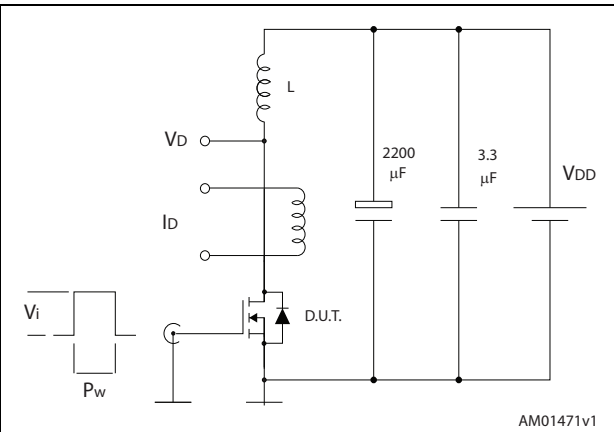
**Figure 16. Gate charge test circuit**



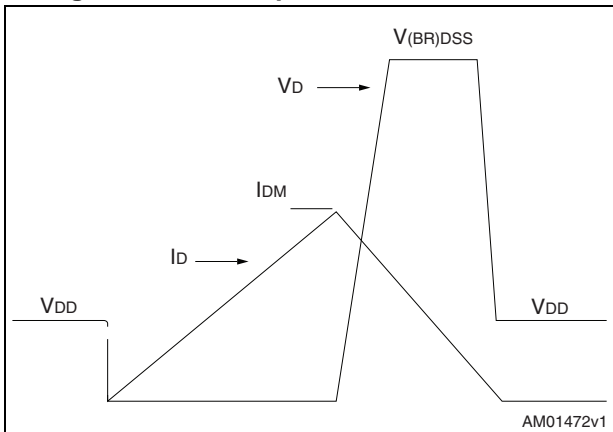
**Figure 17. Test circuit for inductive load switching and diode recovery times**



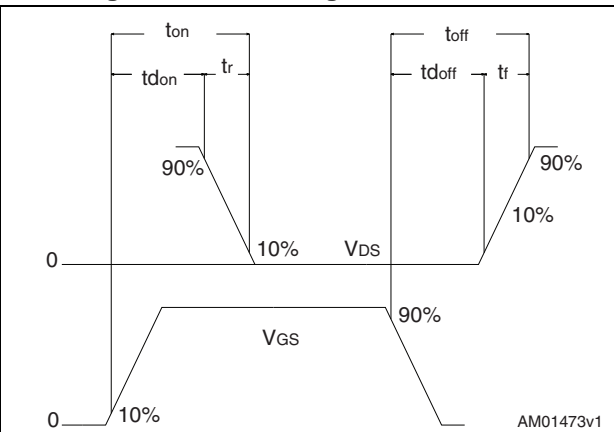
**Figure 18. Unclamped inductive load test circuit**



**Figure 19. Unclamped inductive waveform**



**Figure 20. Switching time waveform**



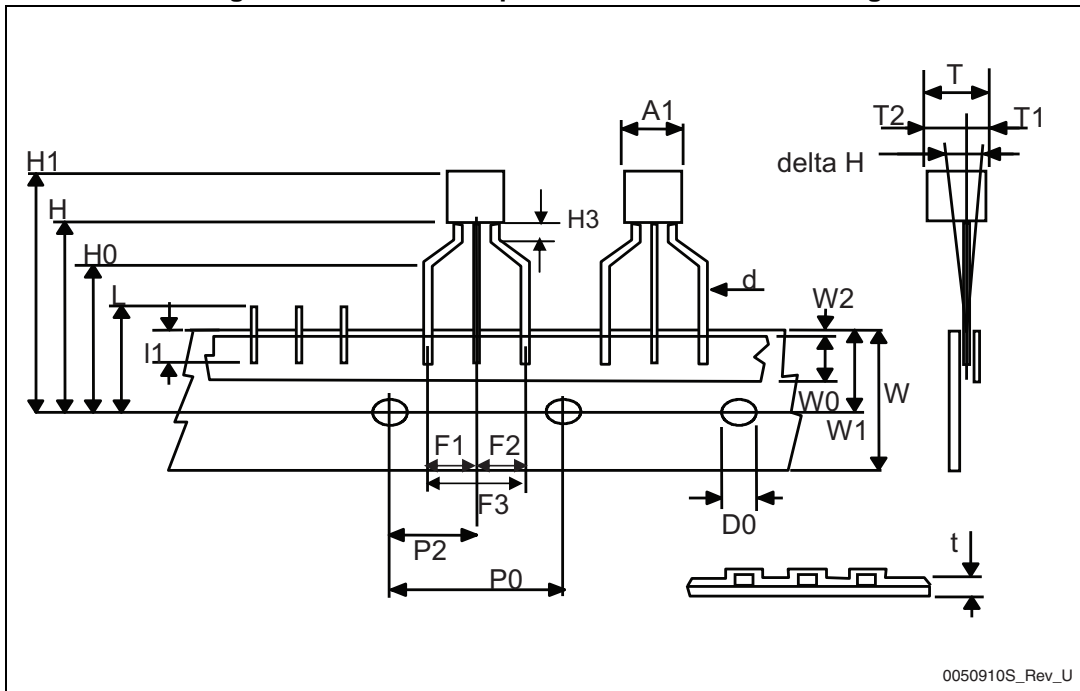
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. TO-92 ammpack mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A1			4.80
T			3.80
T1			1.60
T2			2.30
d	0.45	0.47	0.48
P0	12.50	12.70	12.90
P2	5.65	6.35	7.05
F1, F2	2.40	2.50	2.94
F3	4.98	5.08	5.48
delta H	-2.00		2.00
W	17.50	18.00	19.00
W0	5.5	6.00	6.5
W1	8.50	9.00	9.25
W2			0.50
H		18.50	21
H3	0.5	1	2
H0	15.50	16.00	18.8
H1		25.0	27.0
D0	3.80	4.00	4.20
t			0.90
L			11.00
l1	3.00		
delta P	-1.00		1.00

Figure 21. TO-92 ammpack mechanical data drawing



## 5 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
24-Jun-2013	1	First release. Part number previously included in datasheet DocID17206

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